

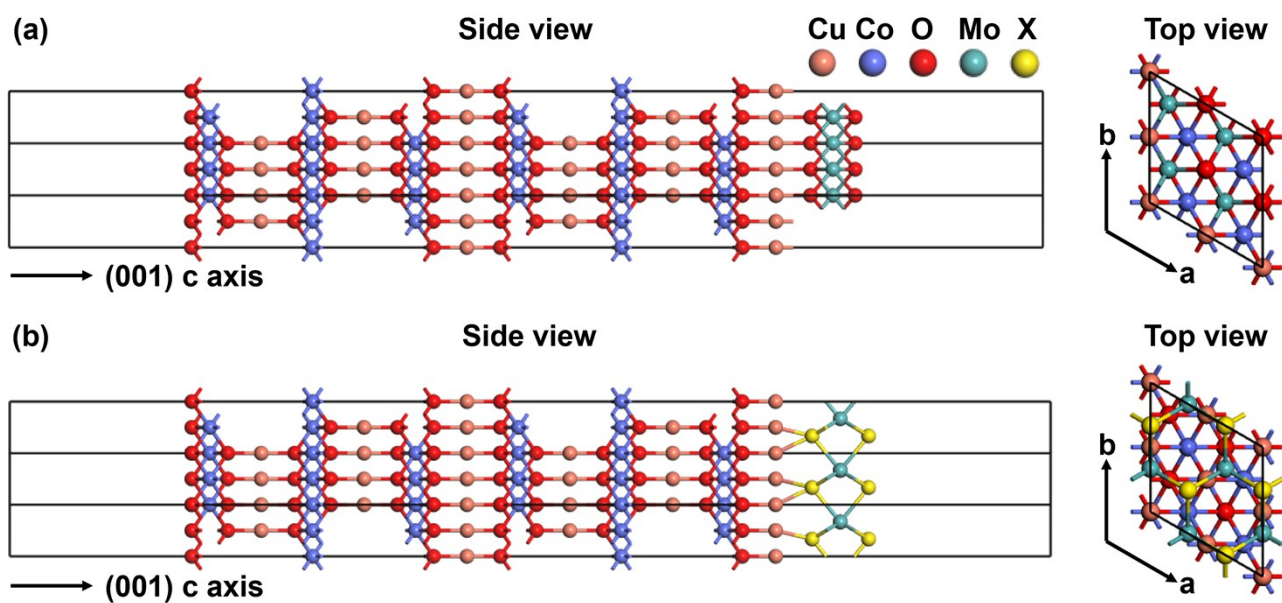
Supplementary information for

**Orbital Hybridization-Induced Direct Z-Scheme in CuCoO₂/MoX₂
Heterostructures for Overcoming Kinetic Imbalance in Overall Water Splitting**

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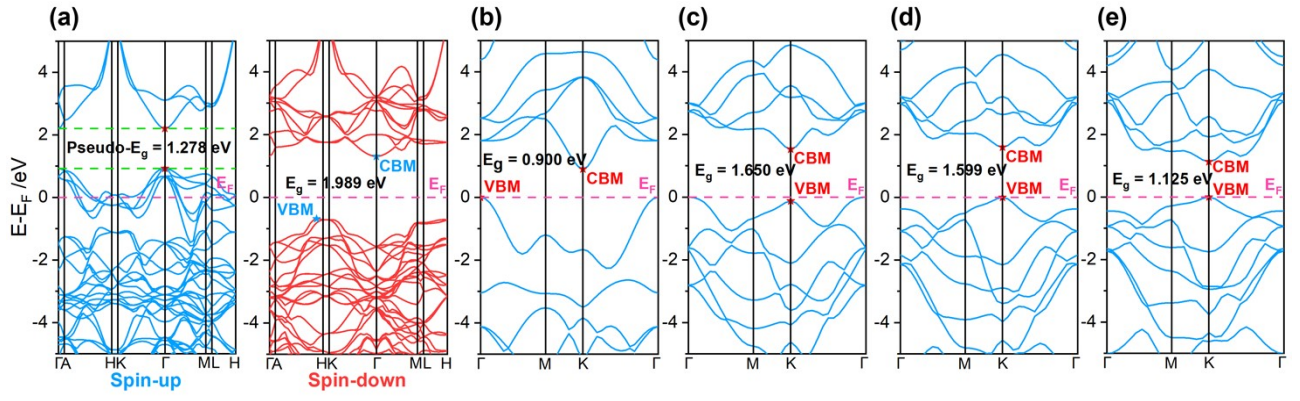


Figure S2. Electronic band structures of (a) bulk CuCoO₂ and monolayer (b) MoO₂, (c) MoS₂, (d) MoSe₂, and (e) MoTe₂.

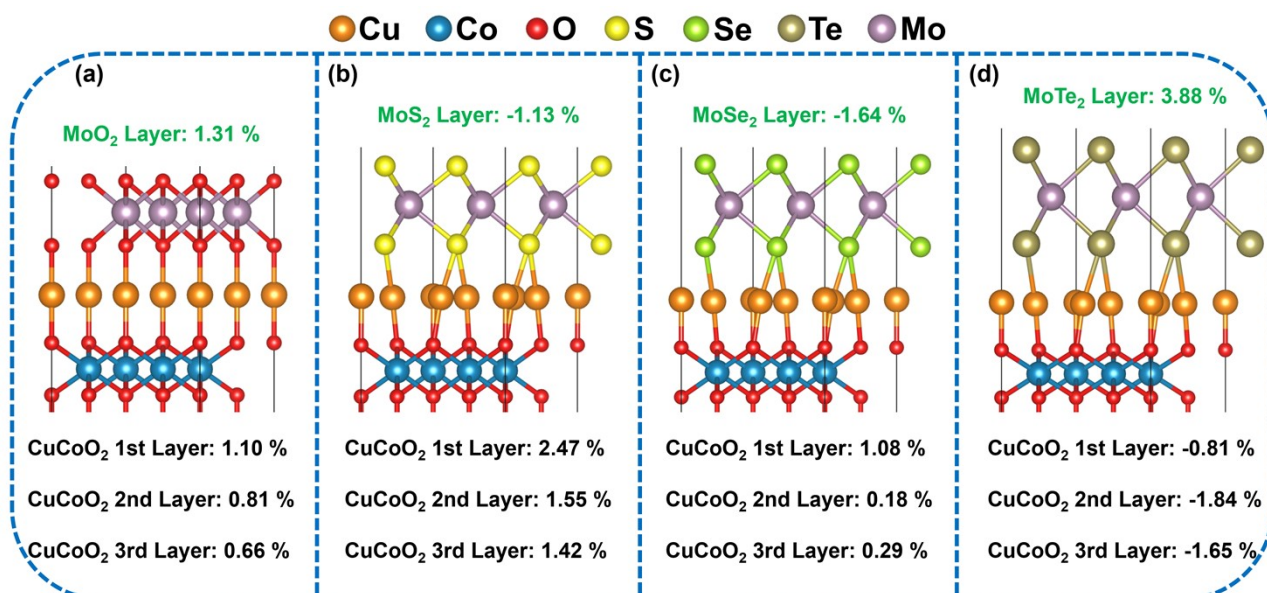


Figure S3. Atomic configurations and layer expansion rates at the interface of (a) CuCoO₂/MoO₂, (b) CuCoO₂/MoS₂, (c) CuCoO₂/MoSe₂, and (d) CuCoO₂/MoTe₂ heterostructures.

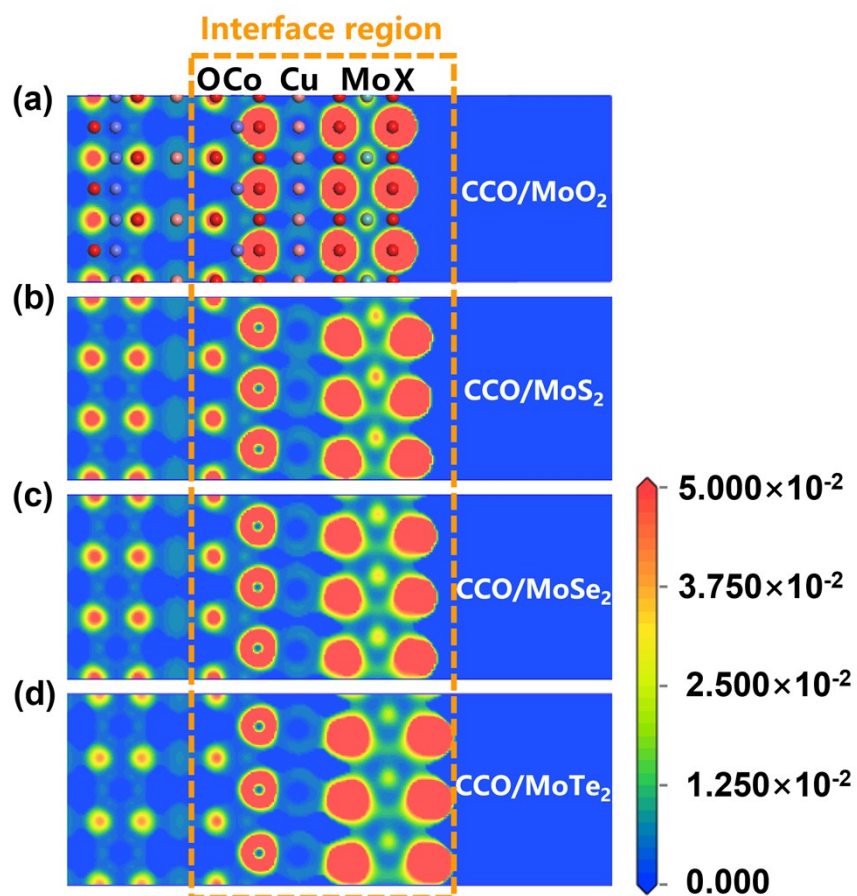


Figure S4. Electron localization function (ELF) cross-sections at the interface of (a) CuCoO₂/MoO₂, (b) CuCoO₂/MoS₂, (c) CuCoO₂/MoSe₂, and (d) CuCoO₂/MoTe₂ heterostructures.

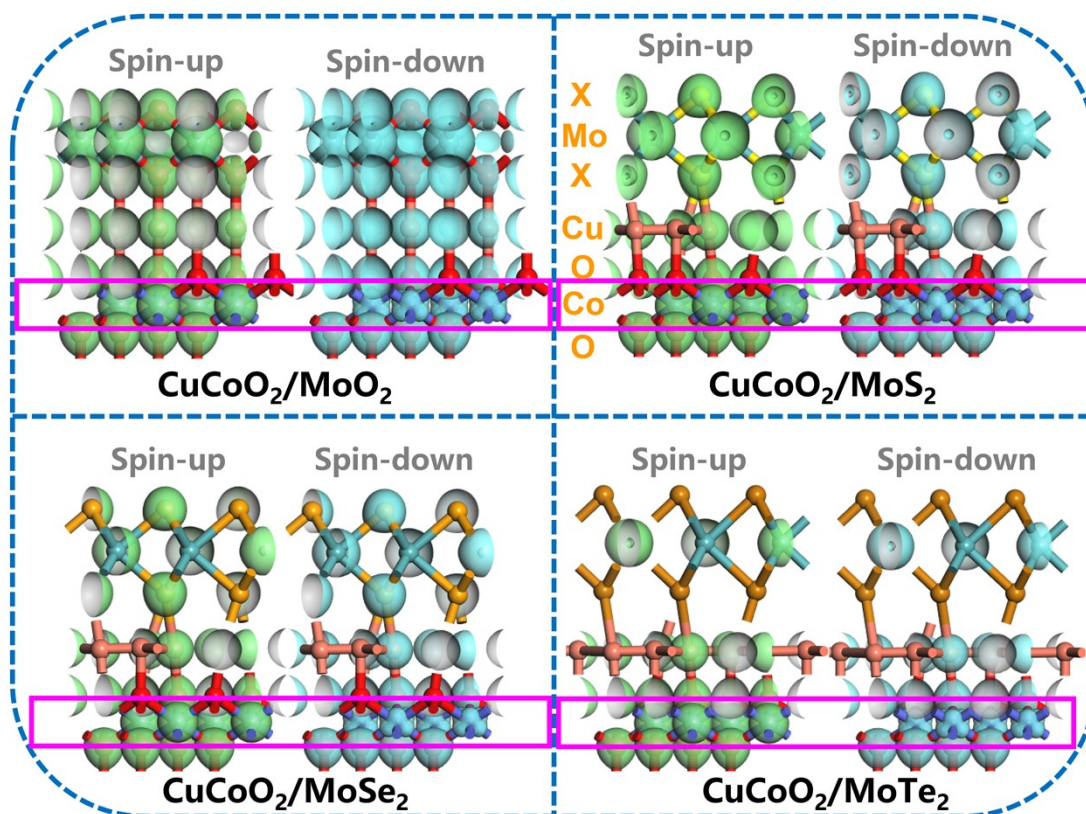


Figure S5. Three-dimensional spin charge density isosurfaces at the interface of $\text{CuCoO}_2/\text{MoX}_2$ heterostructures.

Table S1. Crystal structure parameters of bulk CuCoO₂ and MoX₂ monolayer.

Model	a, b (Å)		c (Å)		Bond length cal. (Å)	
	cal.	exp.	cal.	exp.	Cu–O/Mo–X	M–O
CuCoO ₂	2.896	2.855	16.956	16.916 ¹	1.839	1.942
MoO ₂	2.817	/	/	/	2.035	/
MoS ₂	3.201	3.20 ²	/	/	2.413	/
MoSe ₂	3.286	3.30 ³	/	/	2.532	/
MoTe ₂	3.559	3.52 ⁴	/	/	2.735	/

Table S2. Band edge positions (vs. SHE) and bandgaps of bulk CuCoO₂ and MoX₂ monolayers.

Model	VBM cal. (eV)	CBM cal. (eV)	Band gap ref. (eV)	VBM cal. ref. (eV)	CBM cal. ref. (eV)	VBM exp. (eV)	CBM exp. (eV)
CuCoO ₂	3.12	−0.62	3.74 ¹	3.10	−0.60 ⁵	2.36	−1.38 ¹
MoO ₂	2.269	−0.151	2.42 ⁶	/	/	/	/
MoS ₂	1.424	−1.286	2.71 ⁷	1.84	−0.52 ⁸	1.37	−0.54 ⁹
MoSe ₂	0.802	−1.568	2.37 ⁷	1.18	−0.86 ⁸	0.35	−0.79 ¹⁰
MoTe ₂	0.306	−1.584	1.89 ⁷	0.68	−0.86 ⁸	1.86	−0.81 ¹¹

Table S3. Work function, ΔQ (from the Mulliken population), Electric field (by $\Delta\rho$) direction, and DFT energy of CuCoO₂/MoX₂ heterostructures and their constituent slabs before contact.

Model	Work function Φ /eV	ΔQ of MoX ₂ side /e	Electric field (by $\Delta\rho$) direction	DFT energy /eV
CuCoO ₂ (001) slab (2×2 supercell)	5.456	/	/	−87771.211
MoO ₂ monolayer (2×2 supercell)	6.709	/	/	−11261.689
MoS ₂ monolayer ($\sqrt{3} \times \sqrt{3}$ supercell)	5.864	/	/	−7633.325
MoSe ₂ monolayer ($\sqrt{3} \times \sqrt{3}$ supercell)	5.242	/	/	−26355.692
MoTe ₂ monolayer ($\sqrt{3} \times \sqrt{3}$ supercell)	4.746	/	/	−9239.311
CuCoO ₂ /MoO ₂	5.928	0.24 (gain)	CuCoO ₂ to MoO ₂	−99034.641
CuCoO ₂ /MoS ₂	5.841	−0.14 (loss)	MoS ₂ to CuCoO ₂	−95404.421
CuCoO ₂ /MoSe ₂	5.553	−1.33 (loss)	MoSe ₂ to CuCoO ₂	−114129.004
CuCoO ₂ /MoTe ₂	5.059	−1.41 (loss)	MoTe ₂ to CuCoO ₂	−97016.887

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